

60V N-Channel Power MOSFET

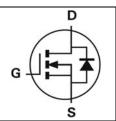
V<sub>DSS</sub>, 60V

 $R_{DS(ON)}$  , 12m $\Omega$  (max.) @ V\_Gs=10V  $R_{DS(ON)}$  , 15m $\Omega$  (max.) @ V\_Gs=4.5V

 $I_D$  , 58A







Description	Features
The SG60N10D series uses advanced Trench technology and designs to provide excellent $R_{\text{DS(ON)}}$ with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.	<ul> <li>Low On-Resistance</li> <li>Low Input Capacitance</li> <li>Low Miller Charge</li> <li>Low Input / Output Leakage</li> </ul>
	Pb-free lead plating; RoHS compliant     Applications
	<ul> <li>Motor / Body Load Control</li> <li>Automotive Systems</li> <li>Load Switch</li> <li>DC-DC converters and Off-line UPS</li> </ul>

**Ordering Information** 

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SG60N10D	Halogen-Free	TO-252	D	Tape & Reel	2,500

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parame	eter	Symbol	Value	Unit
Drain-Source Voltage		V <sub>DS</sub>	60	V
Gate-Source Voltage		V <sub>GS</sub>	±20	V
Drain Compant Continuous	T <sub>C</sub> =25°C		58	А
Drain Current-Continuous	T <sub>C</sub> =100°C	ID I	37	А
Drain Current-Pulsed Note 1		I <sub>DM</sub>	180	А
Maximum Davian Dissination	T <sub>C</sub> =25°C	D	62.5	W
Maximum Power Dissipation	T <sub>C</sub> =70°C	P <sub>D</sub>	40	W
Storage Temperature Range	<u> </u>	Tstg	-55 to +150	°C
Operating Junction Temperature Range		TJ	-55 to +150	°C

**Thermal Resistance Ratings** 

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Maximum Junction-to-Ambient	RθJA	Steady State	-	-	50	°C/W
Maximum Junction-to-Case	R <sub>0</sub> JC	Steady State	-	-	2	°C/W

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#### Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>DS</sub> =250µA	60	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =48V, V <sub>GS</sub> =0V	-	-	1	μΑ
Gate-Body Leakage	Igss	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =250µA	1.2	1.7	2.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>DS</sub> =10A	-	-	12	mΩ
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>DS</sub> =7A	-	-	15	mΩ
Forward Transconductance	gfs	V <sub>DD</sub> =10V, I <sub>DD</sub> =6A	-	11	-	S

DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	C <sub>iss</sub>		-	1364	-	
Output Capacitance	Coss	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, f=1MHz	-	113	-	pF
Reverse Transfer Capacitance	Crss		-	65	-	

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Turn-On Delay Time	T <sub>d(on)</sub>		-	13.5	-	
Rise Time	tr	$V_{GS}$ =10V, $V_{DS}$ =30V, $R_L$ =5 $\Omega$ ,	-	117	-	
Turn-Off Delay Time	T <sub>d(off)</sub>	R <sub>GEN</sub> =3Ω	-	49.8	-	ns
Fall Time	t <sub>f</sub>		-	70	-	
Total Gate Charge	Qg		-	62	-	
Gate to Source Gate Charge	Qgs	V <sub>GS</sub> =10V, V <sub>DS</sub> =30V, I <sub>D</sub> =15A	-	14.4	-	nC
Gate to Drain "Miller" Charge	$Q_{gd}$		-	16.5	-	
Gate resistance	Rg	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	-	13.6	-	Ω

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A	-	-	1.3	V
Continuous Source Current	Is	110 A d1/dt-500 A/us	-	13	-	Α
Pulsed Source Current	Ism	l <sub>F</sub> =12A, dl/dt=500A/μs	-	45	-	Α

#### Notes:

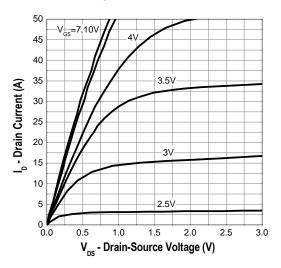
- 1. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 2. R<sub>BJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>BJA</sub> is guaranteed by design while R<sub>BCA</sub> is determined by the user's board design. R<sub>BJA</sub> shown below for single device operation on FR-4 in still air.



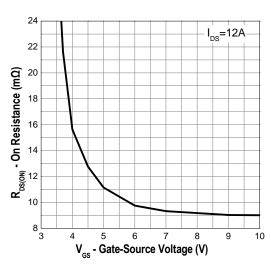
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### **Typical Operating Characteristics**

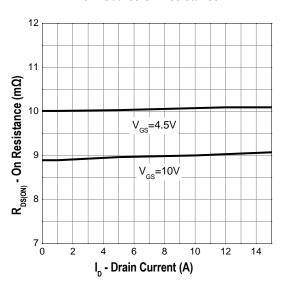
#### **Output Characteristics**



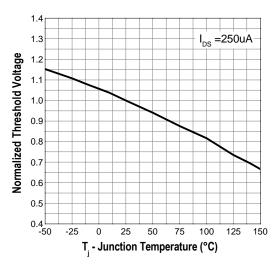
#### **Gate-Source On Resistance**



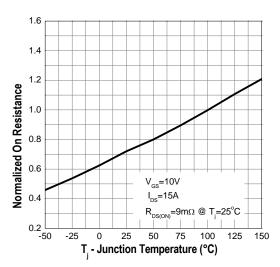
**Drain-Source On Resistance** 



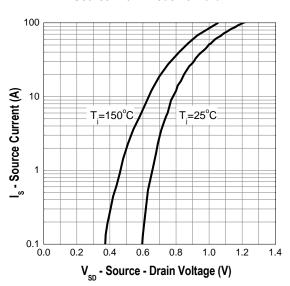
### **Gate Threshold Voltage**



**Drain-Source On Resistance** 



**Source-Drain Diode Forward** 

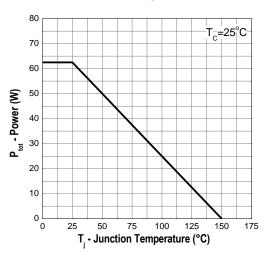




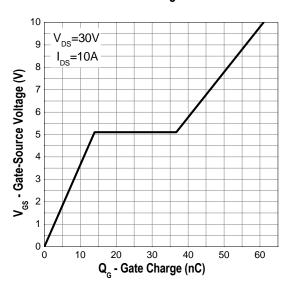
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### **Typical Operating Characteristics (Cont.)**

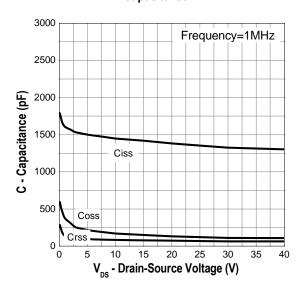
#### **Power Dissipation**



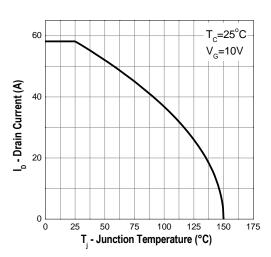
#### **Gate Charge**



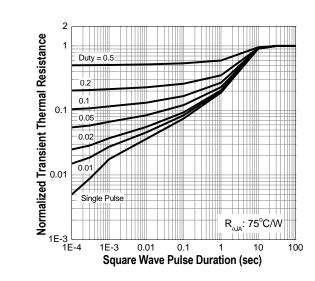
#### Capacitance



#### **Drain Current**



#### **Transient Thermal Impedance**





**SG60N10D** 60V N-Channel Power MOSFET

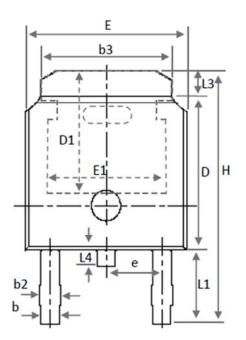
## **Marking Information**

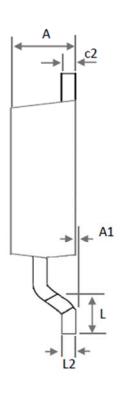
TO-252 (D)	Marking Rule
SG60N10D YYMMXXX	Line 1 : Device SG60N10D  Line 2 : Date Code YYMMXXX  YY : Year Code MM : Month Code XXX : Serial Number
Diagram	



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### **Package of Dimension**





Symbol	Min	Nor	Max
E	6.35	6.54	6.731
L	1.40	1.59	1.78
L1		2.743 Ref	
L2	(	0.508 BSC	Ĉ.
L3	0.89	1.08	1.27
L4	0.60	0.81	1.01
D	5.97	6.10	6.223
Н	9.40	9.91	10.41
b	0.64	0.77	0.89
b2	0.76	0.95	1.14
b3	4.95	5.21	5.46
е		2.286 BSC	0
Α	2.18	2.29	2.39
A1	0.00	0.07	0.13
c2	0.46	0.68	0.89
D1	5.21	-	-
E1	4.32	-	-

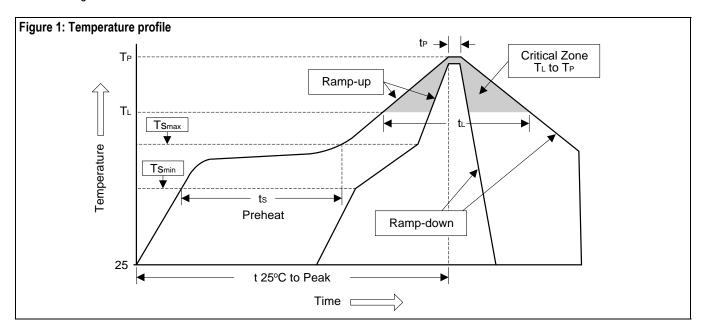
- 1. All dimension are in millimeters.
- 2. Dimension does not include burrs and mold flash/protrusions.



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### Soldering Methods for Silicongear's Products

- 1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
- 2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T <sub>L</sub> to T <sub>P</sub> )	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (Ts <sub>min</sub> )	100°C	150°C
- Temperature Max (Ts <sub>max</sub> )	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
Tsmax to T∟		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T∟)	183°C	217°C
- Time (t∟)	60 to 150 sec	60 to 150 sec
Peak Temperature (T <sub>P</sub> )	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak	10 to 30 sec	20 to 40 sec
Temperature (t₂)	10 to 50 sec	20 to 40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec



SG60N10D
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